

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuhiko HATANO et al.

Application No.: New U.S. National Stage of PCT/JP2004/017099

Filed: May 16, 2006

Docket No.: 128029

For: HIGH VOLTAGE PULSE GENERATING CIRCUIT

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

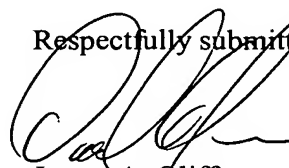
Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 17 & 26.
- ☒ 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 16 & 24-25.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. A partial English language Translation of one or more non-English language reference is attached hereto. See Reference 30.
- ☒ 6. An English language Abstract of one or more non-English language reference is attached hereto. See References 16-17, 20-22 & 24-26.
- ☒ 7. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 16-17 & 20-25.

IAP20 Rec'd PCT/PTO 16 MAY 2006

- ☒ 8. One or more co-pending U.S. patent application is identified on the attached Form PTO 1449. The Examiner is respectfully requested to consider each cited application and the art cited therein during examination of the present application.
- ☒ 9. Reference 1 corresponds to reference 16. Reference 12 corresponds to reference 24.

Respectfully submitted,



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Form PTO-1449 (REV. 1/06) <div style="text-align: center; margin-top: 10px;"> US Dept. of Commerce PATENT & TRADEMARK OFFICE </div> <div style="text-align: center; margin-top: 10px;"> INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) </div>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 60%;"> ATTY DOCKET NO. 128029 </td> <td style="width: 40%;"> APPLICATION NO. New U.S. Patent Application 802,229,357 </td> </tr> <tr> <td colspan="2"> APPLICANTS Tatsuhiko HATANO et al. </td> </tr> <tr> <td> FILING DATE May 16, 2006 </td> <td> </td> </tr> </table>	ATTY DOCKET NO. 128029	APPLICATION NO. New U.S. Patent Application 802,229,357	APPLICANTS Tatsuhiko HATANO et al.		FILING DATE May 16, 2006	
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APPLICANTS Tatsuhiko HATANO et al.							
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U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Date	Name
	1.	2003/0230938 A1	12/18/2003	HATANO et al.
	2.	2003/0209993 A1	11/13/2003	ITO et al.
	3.	4,740,722	04/26/1988	FURUHATA
	4.	5,151,762	09/29/1992	UENISHI et al.
	5.	5,774,348	06/30/1998	DRUCE et al.
	6.	3,510,676	05/05/1970	PIERCE
	7.	3,877,864	04/15/1975	CARLSON
	8.	3,176,158	03/30/1965	GUIGNARD
	9.	3,671,761	06/20/1972	SHIBUYA et al.
	10.	3,485,227	12/23/1969	MEYERLE
	11.	3,367,314	02/06/1968	HIROSAWA et al.
	12.	5,627,741	05/06/1997	NARUO et al.
	13.	11/293,324 (Attny Dckt 126712)	12/05/2005	SEKIYA et al.
	14.	10/576,253 (Attny Dckt 127737)	04/17/2006	HATANO et al.
	15.	11/405,698 (Attny Dckt 127772)	04/17/2006	HATANO et al.

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation
	16.	JP-A-2004-072994	03/04/2004	JAPAN	X	X

OTHER DOCUMENTS

Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER	DATE CONSIDERED
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Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: May 16, 2006

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 128029		APPLICATION NO. New U.S. Patent Application 00/579557	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Tatsuhiko HATANO et al.			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	17.	JP-A-2002-044965	02/08/2002	JAPAN	X	X	
	18.	EP 0 959 562 A1	11/24/1999	EUROPE			
	19.	GB 2 105 927 A	03/30/1983	UNITED KINGDOM			
	20.	JP-A-2003-272887	09/26/2003	JAPAN	X	X	
	21.	JP-A-10-76182	03/24/1998	JAPAN	X	X	
	22.	JP-A-11-145793	05/28/1999	JAPAN	X	X	
	23.	JP-B2-2649340	05/16/1997	JAPAN			X
	24.	JP-A-08-223915	08/30/1996	JAPAN	X	X	
	25.	JP-A-2003-338648	11/28/2003	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	26.	IIDA et al., "Ultra Short-width High-Voltage Pulse Generator"; The Institute of Electrical Engineers of Japan; Plasma Science and Technology; Dept. of Manufacturing Engineering NGK Insulators, Ltd.; Lecture No. PST-02-16.(w/ abstract)					
	27.	JIANG et al., "Compact, High Repetition-Rate Pulsed Power Generator Using High-Speed Si-Thyristor"; <i>IEEE</i> ; pp. 602-604; June 30, 2002; Conference Record of the 25 th International Power Modulator Symposium and 2002 High-Voltage Workshop: July 30-July 3, 2002.					
	28.	YAMASHITA et al., "High Rep-Rate Inductive-Energy-Storage Pulsed Power Modulator Using High Voltage Static Induction Thyristor"; <i>IEEE</i> ; pp. 382-385; June 30, 2002; Conference Record of the 25 th International Power Modulator Symposium and 2002 High-Voltage Workshop: June 30-July 3 2002.					
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OTHER DOCUMENTS		
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)
	29.	BOWLES et al., "30 kA, 5000 V Solid State Opening Switch for Inductive Energy Stores"; <i>IEEE</i> ; Vol. 20; pp. 249-253; June 23, 1992; Proceedings of the Power Modulator Symposium: June 23-25, 1992.
	30.	ICHIKAWA et al.; "Deposition of a-Si: H Based film by high voltage pulse discharge CVD"; <i>Oyo Buturi</i> ; Vol. 61, No. 10; Japan Society of Applied Physics; 1992. (w/ partial trans)
	31.	NAMIHIRA et al.; "Improvement of NO _x Removal Efficiency Using Short-Width Pulsed Power"; <i>IEEE Transactions on Plasmic Science</i> ; Vol. 28, No. 2; pg. 434-442; April 2000.

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